FORM PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION				DOCKET NUMBER SLA0805	1	APPLICATION NUMBER		
				APPLICANT Wei Gao, and Yoshi Ono				
				FILING DATE: September 30, 20			GROUP ART UNIT	
		U.S. PAT	ENT D	OCUMENTS				
EXAMINER INITIAL	DOCUMENT NUMBER	DATE		NAME	CLA	.ss	SUB CLASS	FILE. DATE IF APPROP.
		FOREIGN P.	'ATEN	T DOCUMENTS				
	DOCUMENT NUMBER	DATE		COUNTRY/NAME	CLA	SS	SUB CLASS	TRANSLATION YES NO
OTHER DOCUMENTS								
SL	Article entitled: Nb Oxide Thin Film Resistors; by Wilson et al., published in IEEE Transactions on Applied Superconductivity, Vol.9 No. 2, June 1999.							
SL	Article entitled: Properties of Ru-Ta Alloys as Gate Electrodes For NMOS and PMOS Silicon Devices, by Zhong et al., IEEE, 2001							
SL	Article entitled: Tunable Work Function Molybdenum Gate Technology for FDSOI-CMOS, by Ranade et al., IEEE 2002							
SL	Article entitled: A Phase Map for Sputter Deposited Niobium Oxides, by Lee and Aita, pub in the Journal of Applied Physics, Vol. 70, No. 4, 15 August 1991							
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